

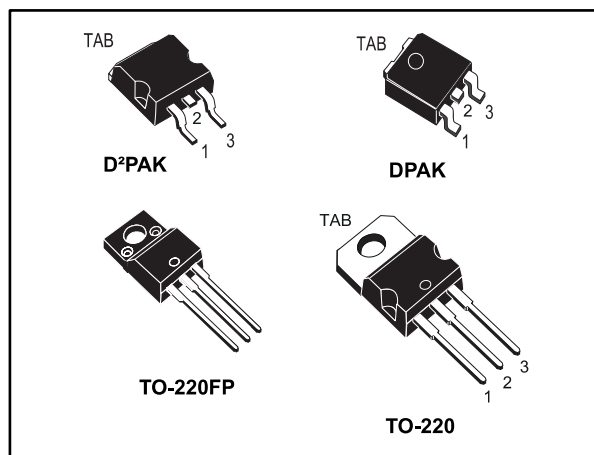
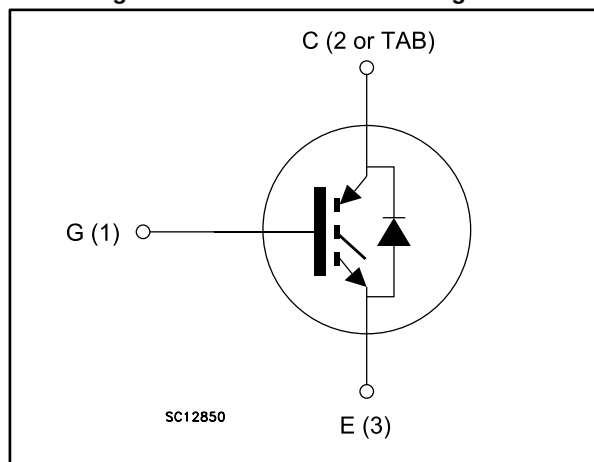


Figure 1: Internal schematic diagram



Features

- Minimal tail current
- Low conduction and switching losses
- Ultrafast soft recovery antiparallel diode

Applications

- Motor drive

Description

These devices are based on a new advanced planar technology concept to yield an IGBT with more stable switching performance (E_{off}) versus temperature, as well as lower conduction losses.

Table 1: Device summary

Order code	Marking	Package	Packing
STGB3HF60HD	GB3HF60HD	D²PAK	Tape and reel
STGD3HF60HDT4	GD3HF60HD	DPAK	Tape and reel
STGF3HF60HD	GF3HF60HD	TO-220FP	Tube
STGP3HF60HD	GP3HF60HD	TO-220	Tube

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1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value			Unit
		DPAK	D ² PAK TO-220	TO-220FP	
V _{CES}	Collector-emitter voltage (V _{GE} = 0)	600			V
I _C ⁽¹⁾	Continuous collector current at T _C = 25 °C	7.5			A
I _C ⁽¹⁾	Continuous collector current at T _C = 100 °C	4.5			A
I _{CL} ⁽²⁾	Turn-off latching current	18			A
I _{CP} ⁽³⁾	Pulsed collector current	18			A
V _{GE}	Gate-emitter voltage	± 20			V
I _F	Diode RMS forward current at T _C = 25 °C	10			A
I _{FSM}	Surge non repetitive forward current t _p = 10 ms sinusoidal	25			A
P _{TOT}	Total dissipation at T _C = 25 °C	38		18	W
T _{STG}	Storage temperature range	- 55 to 150			°C
T _J	Operating junction temperature range				

Notes:

⁽¹⁾Calculated according to the iterative formula:

$$I_C(T_C) = \frac{T_{j(max)} - T_C}{R_{thj-c} \times V_{CE(sat)(max)}(T_{j(max)}, I_C(T_C))}$$

⁽²⁾V_{clamp} = 80 %, (V_{CES}), T_J = 150 °C, R_G = 10 Ω, V_{GE} = 15 V.

⁽³⁾Pulse width limited by maximum junction temperature range.

Table 3: Thermal data

Symbol	Parameter	Value			Unit
		DPAK	D ² PAK TO-220	TO-220FP	
R _{thj-case}	Thermal resistance junction-case IGBT	3.3		6.9	°C/W
	Thermal resistance junction-case diode	5		8	°C/W
R _{thj-amb}	Thermal resistance junction-ambient	100	62.5		°C/W

2 Electrical characteristics

($T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise specified).

Table 4: Static electrical characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage ($V_{GE} = 0$)	$I_C = 1\text{ mA}$	600			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}$, $I_C = 0.5\text{ A}$, $T_J = 125\text{ }^{\circ}\text{C}$		1.4		V
		$V_{GE} = 15\text{ V}$, $I_C = 1.5\text{ A}$		2.45	2.95	
		$V_{GE} = 15\text{ V}$, $I_C = 1.5\text{ A}$, $T_J = 125\text{ }^{\circ}\text{C}$		1.85		
$V_{GE(th)}$	Gate threshold voltage	$V_{CE} = V_{GE}$, $I_C = 250\text{ }\mu\text{A}$	3.75		5.75	V
I_{CES}	Collector cut-off current ($V_{GE} = 0$)	$V_{CE} = 600\text{ V}$			250	μA
		$V_{CE} = 600\text{ V}$, $T_J = 125\text{ }^{\circ}\text{C}$			1	mA
I_{GES}	Gate-emitter leakage current ($V_{CE} = 0$)	$V_{GE} = \pm 20\text{ V}$			± 100	nA
g_{fs}	Forward transconductance	$V_{CE} = 15\text{ V}$, $I_C = 1.5\text{ A}$		1.5		S

Table 5: Dynamic electrical characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies}	Input capacitance	$V_{CE} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GE} = 0$	-	152	-	pF
C_{oes}	Output capacitance		-	14	-	pF
C_{res}	Reverse transfer capacitance		-	3	-	pF
Q_g	Total gate charge	$V_{CE} = 480\text{ V}$, $I_C = 1.5\text{ A}$, $V_{GE} = 15\text{ V}$ (see Figure 18: "Gate charge test circuit")	-	12	-	nC
Q_{ge}	Gate-emitter charge		-	2	-	nC
Q_{gc}	Gate-collector charge		-	6	-	nC

Table 6: Switching on/off (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{CC} = 400\text{ V}$, $I_C = 1.5\text{ A}$ $R_G = 100\ \Omega$, $V_{GE} = 15\text{ V}$ (see Figure 17: "Test circuit for inductive load switching" Figure 19: "Switching waveform")	-	11	-	ns
t_r	Current rise time		-	4	-	ns
$(di/dt)_{on}$	Turn-on current slope		-	285	-	A/ μ s
$t_{d(on)}$	Turn-on delay time	$V_{CC} = 400\text{ V}$, $I_C = 1.5\text{ A}$ $R_G = 100\ \Omega$, $V_{GE} = 15\text{ V}$, $T_j = 125\text{ }^\circ\text{C}$ (see Figure 17: "Test circuit for inductive load switching" Figure 19: "Switching waveform")	-	10	-	ns
t_r	Current rise time		-	5	-	ns
$(di/dt)_{on}$	Turn-on current slope		-	265	-	A/ μ s
$t_r(V_{off})$	Off voltage rise time	$V_{CC} = 400\text{ V}$, $I_C = 1.5\text{ A}$, $R_{GE} = 100\ \Omega$, $V_{GE} = 15\text{ V}$ (see Figure 17: "Test circuit for inductive load switching" Figure 19: "Switching waveform")	-	26	-	ns
$t_d(off)$	Turn-off delay time		-	60	-	ns
t_f	Current fall time		-	50	-	ns
$t_r(V_{off})$	Off voltage rise time	$V_{CC} = 400\text{ V}$, $I_C = 1.5\text{ A}$, $R_{GE} = 100\ \Omega$, $V_{GE} = 15\text{ V}$, $T_j = 125\text{ }^\circ\text{C}$ (see Figure 17: "Test circuit for inductive load switching" Figure 19: "Switching waveform")	-	64	-	ns
$t_d(off)$	Turn-off delay time		-	69	-	ns
t_f	Current fall time		-	71	-	ns

Table 7: Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$E_{on(1)}$	Turn-on switching energy	$V_{CC} = 400\text{ V}$, $I_C = 1.5\text{ A}$ $R_G = 100\ \Omega$, $V_{GE} = 15\text{ V}$ (see Figure 17: "Test circuit for inductive load switching" Figure 19: "Switching waveform")	-	19	-	μ J
$E_{off(2)}$	Turn-off switching energy		-	12	-	μ J
E_{ts}	Total switching energy		-	31	-	μ J
$E_{on(1)}$	Turn-on switching energy	$V_{CC} = 400\text{ V}$, $I_C = 1.5\text{ A}$ $R_G = 100\ \Omega$, $V_{GE} = 15\text{ V}$, $T_j = 125\text{ }^\circ\text{C}$ (see Figure 17: "Test circuit for inductive load switching" Figure 19: "Switching waveform")	-	38	-	μ J
$E_{off(2)}$	Turn-off switching energy		-	35	-	μ J
E_{ts}	Total switching energy		-	73	-	μ J

Notes:

(1) E_{on} is the turn-on energy when a typical diode is used in the test circuit in [Figure 17: "Test circuit for inductive load switching"](#). If the IGBT is offered in a package with a co-pak diode, the co-pak diode is used as external diode. IGBTs and diode are at the same temperature (25 °C and 125 °C).

(2)Turn-off energy include also the tail of the collector current.

Table 8: Collector-emitter diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_F	Forward on-voltage	$I_F = 1.5 \text{ A}$	-	1.4	1.8	V
		$I_F = 1.5 \text{ A}, T_j = 125 \text{ }^\circ\text{C}$	-	1.15		
t_{rr}	Reverse recovery time	$I_F = 1.5 \text{ A}, V_R = 40 \text{ V},$ $di/dt = 100 \text{ A}/\mu\text{s}$ (see Figure 20: "Diode reverse recovery waveform")	-	85		ns
Q_{rr}	Reverse recovery charge		-	124		nC
I_{rrm}	Reverse recovery current		-	3		A
t_{rr}	Reverse recovery time	$I_F = 1.5 \text{ A}, V_R = 40 \text{ V},$ $T_j = 125 \text{ }^\circ\text{C}, di/dt = 100 \text{ A}/\mu\text{s}$ (see Figure 20: "Diode reverse recovery waveform")	-	114		ns
Q_{rr}	Reverse recovery charge		-	194		nC
I_{rrm}	Reverse recovery current		-	3.5		A

2.1 Electrical characteristics (curves)

Figure 2: Output characteristics

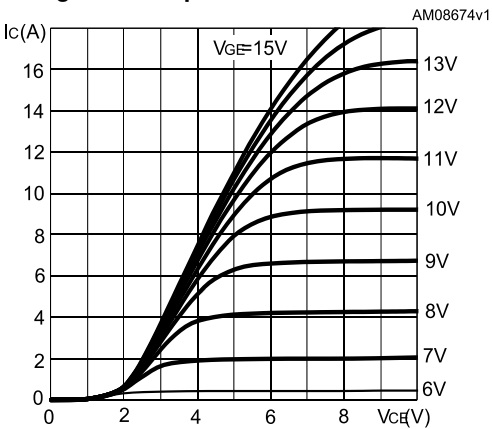


Figure 3: Output characteristic details

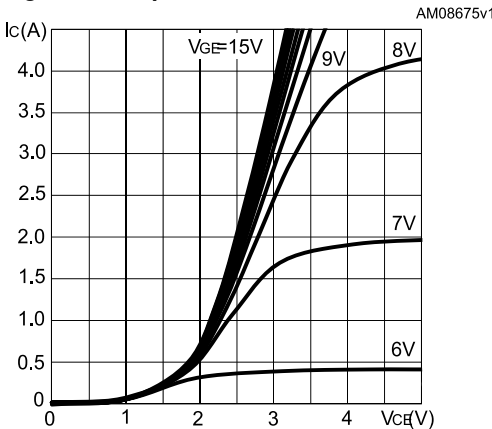


Figure 4: Transfer characteristics

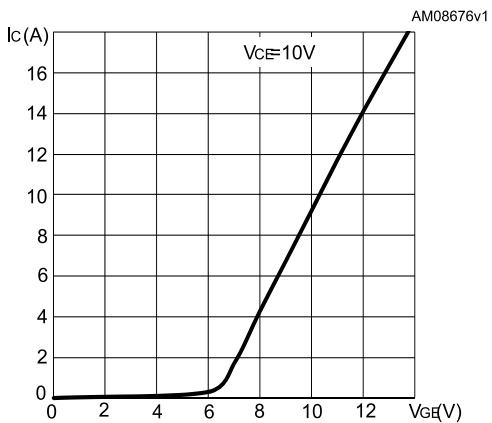


Figure 5: Collector-emitter on voltage vs collector current

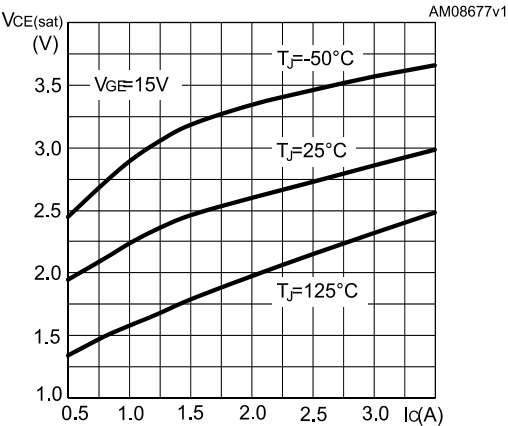


Figure 6: Collector-emitter on voltage vs temperature

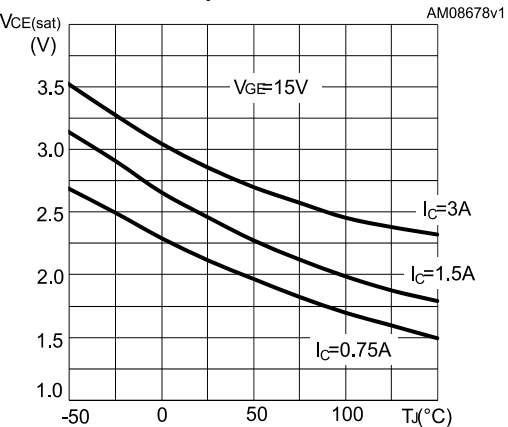


Figure 7: Breakdown voltage vs temperature

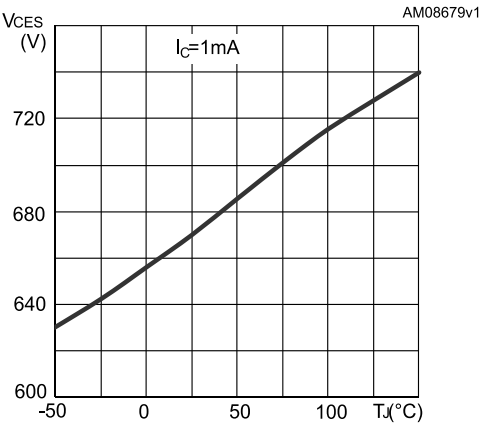


Figure 8: Gate threshold voltage vs temperature

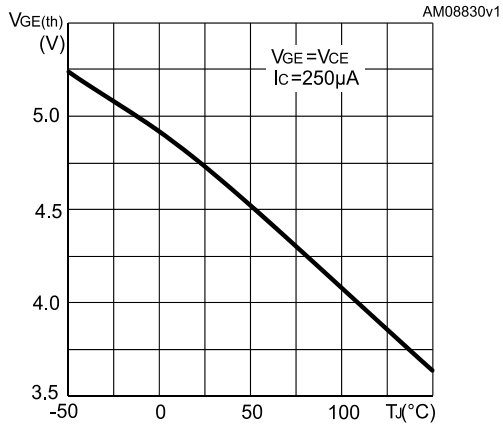


Figure 9: Gate charge vs gate-emitter voltage

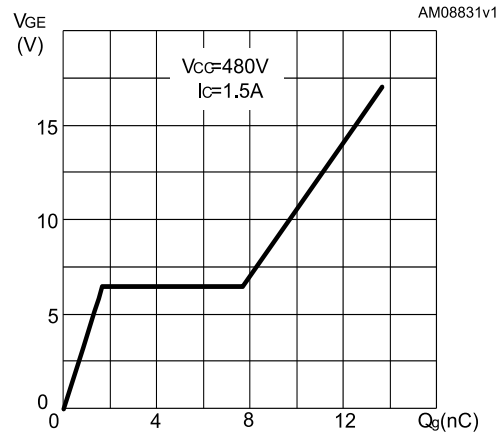


Figure 10: Capacitance variations

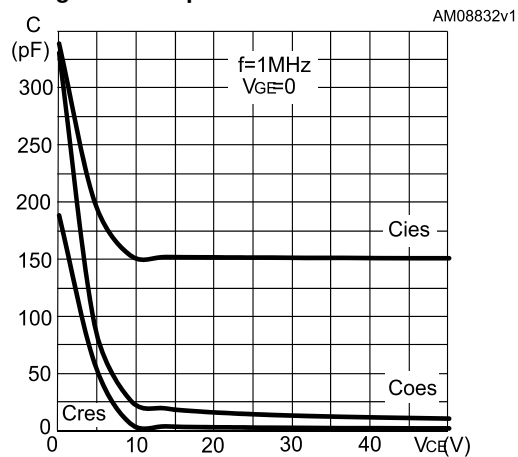


Figure 11: Switching energy vs collector current

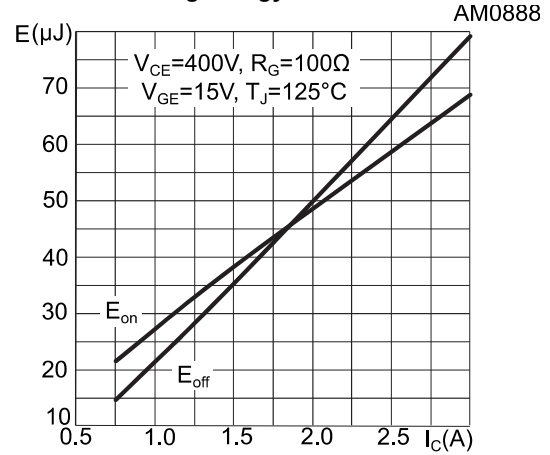


Figure 12: Switching energy vs gate resistance

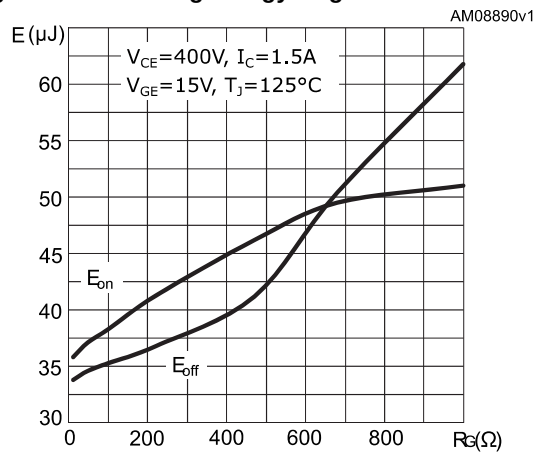


Figure 13: Switching energy vs temperature

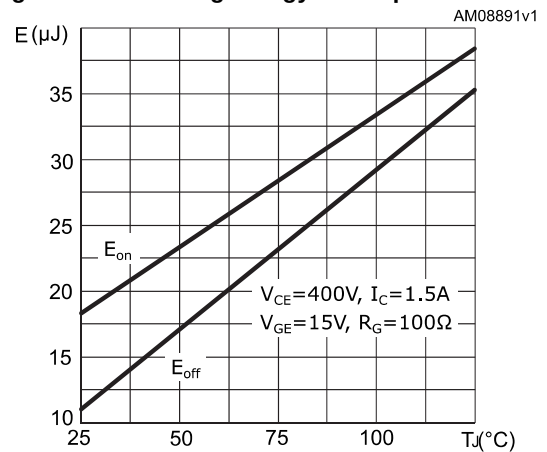


Figure 14: Turn-off SOA

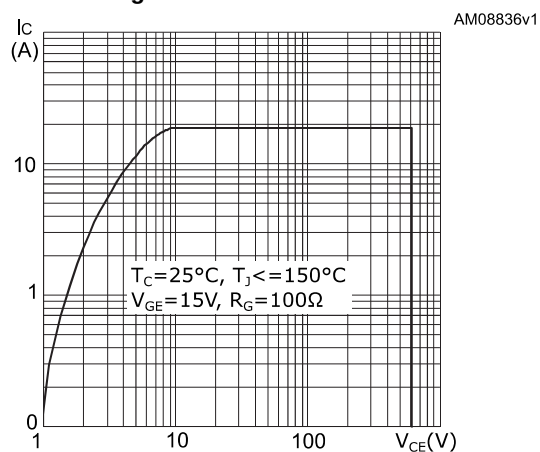


Figure 15: Diode forward on voltage

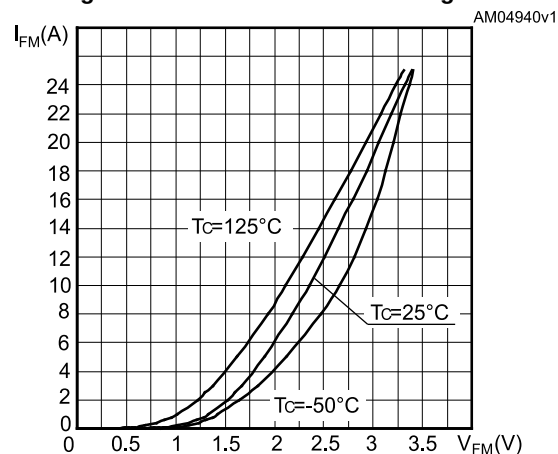
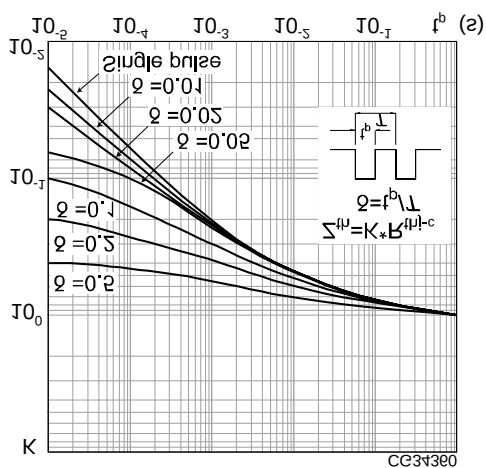
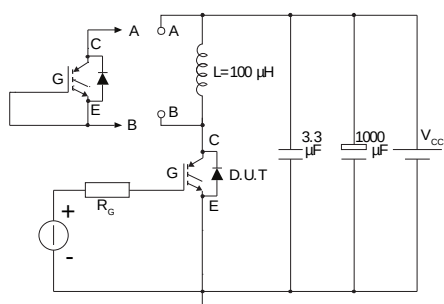


Figure 16: Thermal impedance



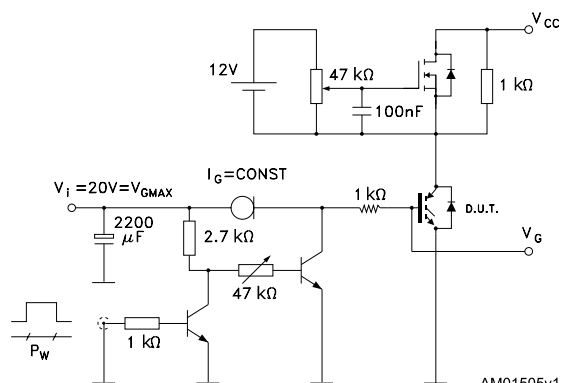
3 Test circuits

Figure 17: Test circuit for inductive load switching



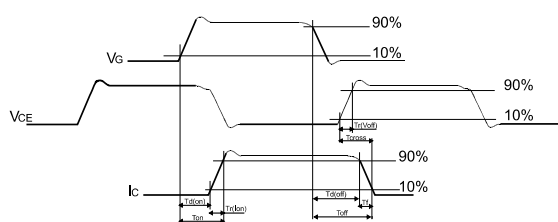
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Figure 18: Gate charge test circuit



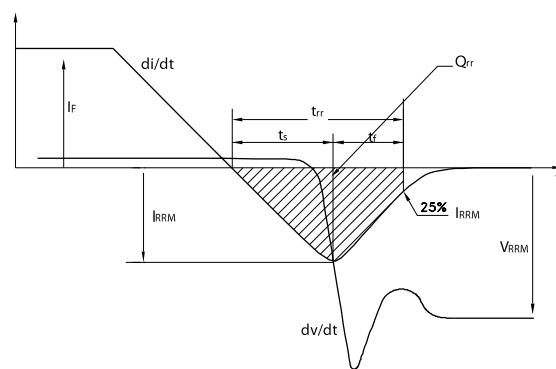
AM01505v1

Figure 19: Switching waveform



AM01506v1

Figure 20: Diode reverse recovery waveform



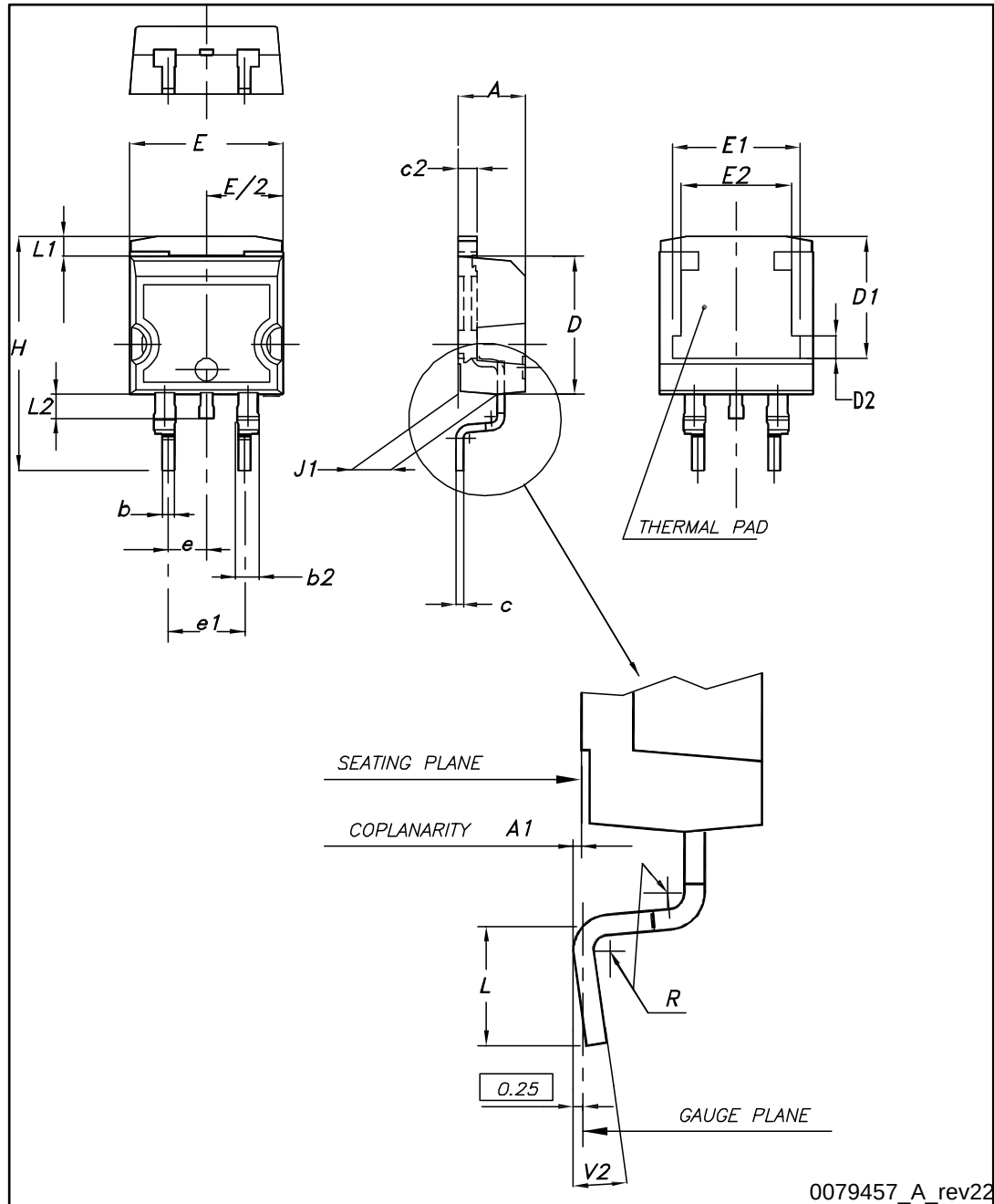
AM01507v1

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

4.1 D²PAK (TO-263) package information

Figure 21: D²PAK (TO-263) type A package outline

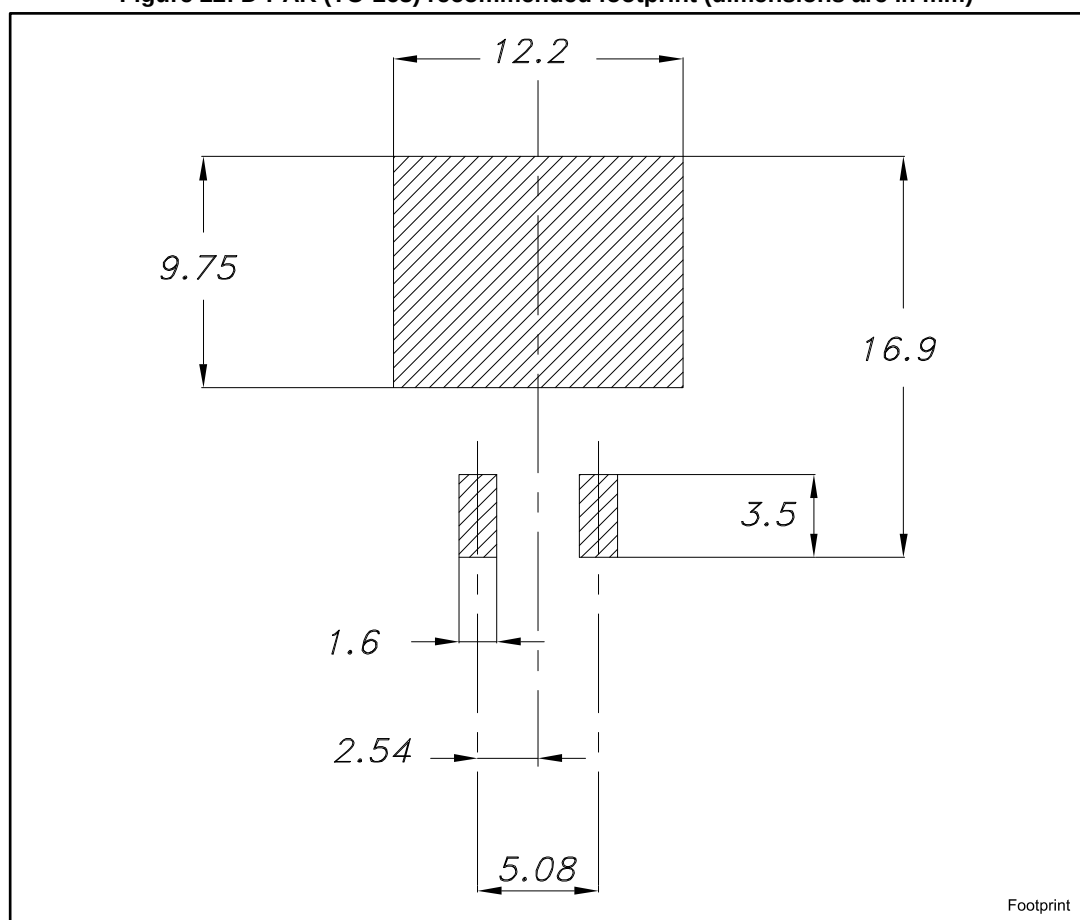


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Table 9: D²PAK (TO-263) type A package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50	7.75	8.00
D2	1.10	1.30	1.50
E	10		10.40
E1	8.50	8.70	8.90
E2	6.85	7.05	7.25
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

Figure 22: D²PAK (TO-263) recommended footprint (dimensions are in mm)



4.2 D²PAK (TO-263) packing information

Figure 23: Tape outline

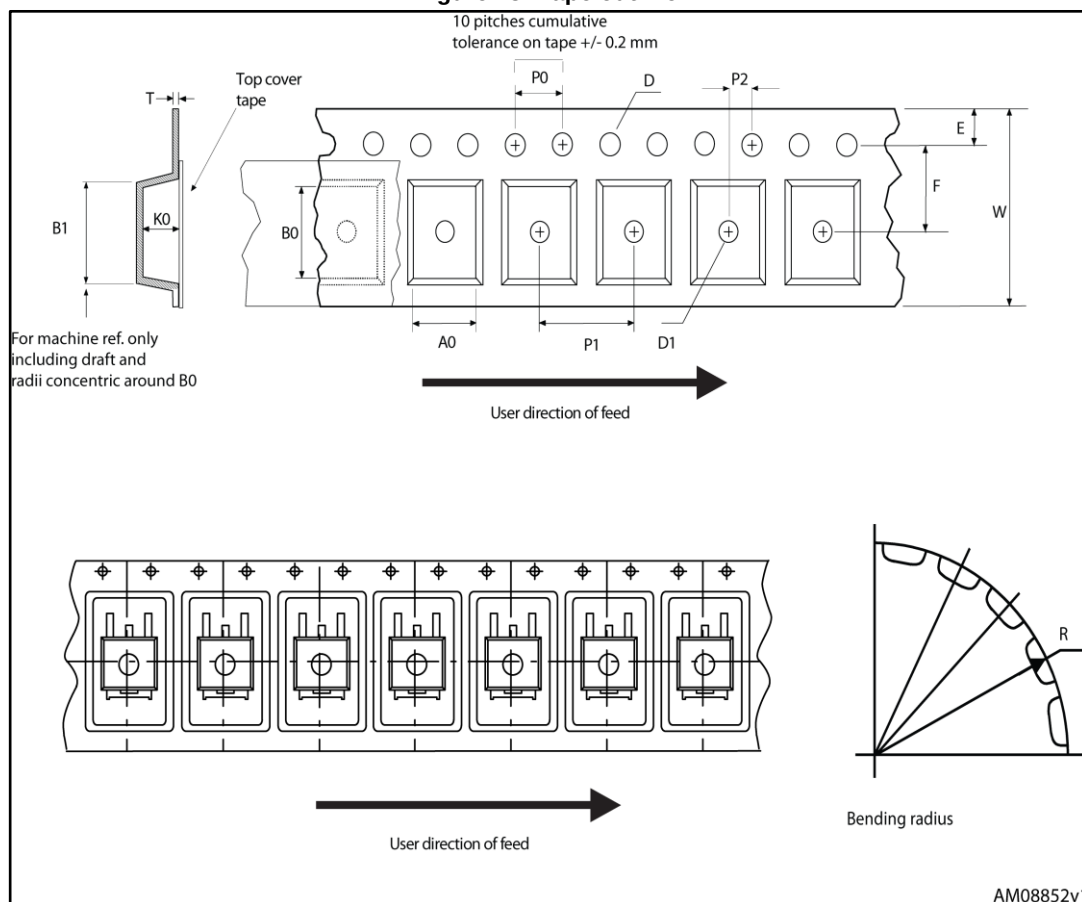


Figure 24: Reel outline

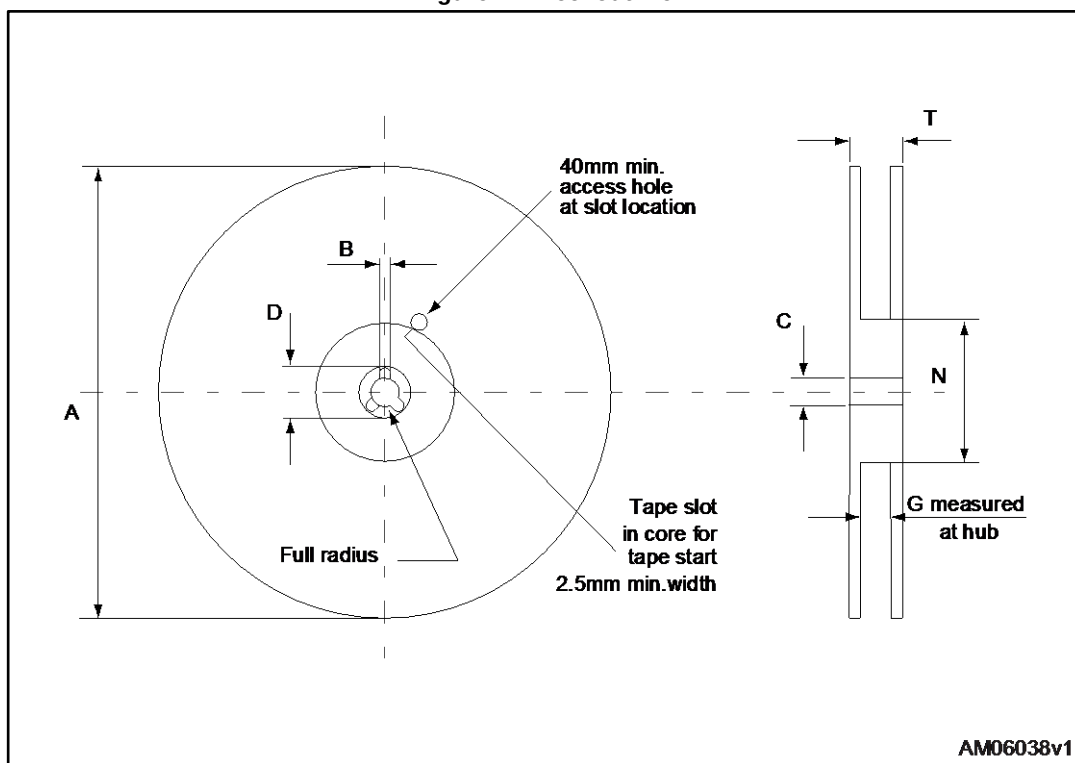
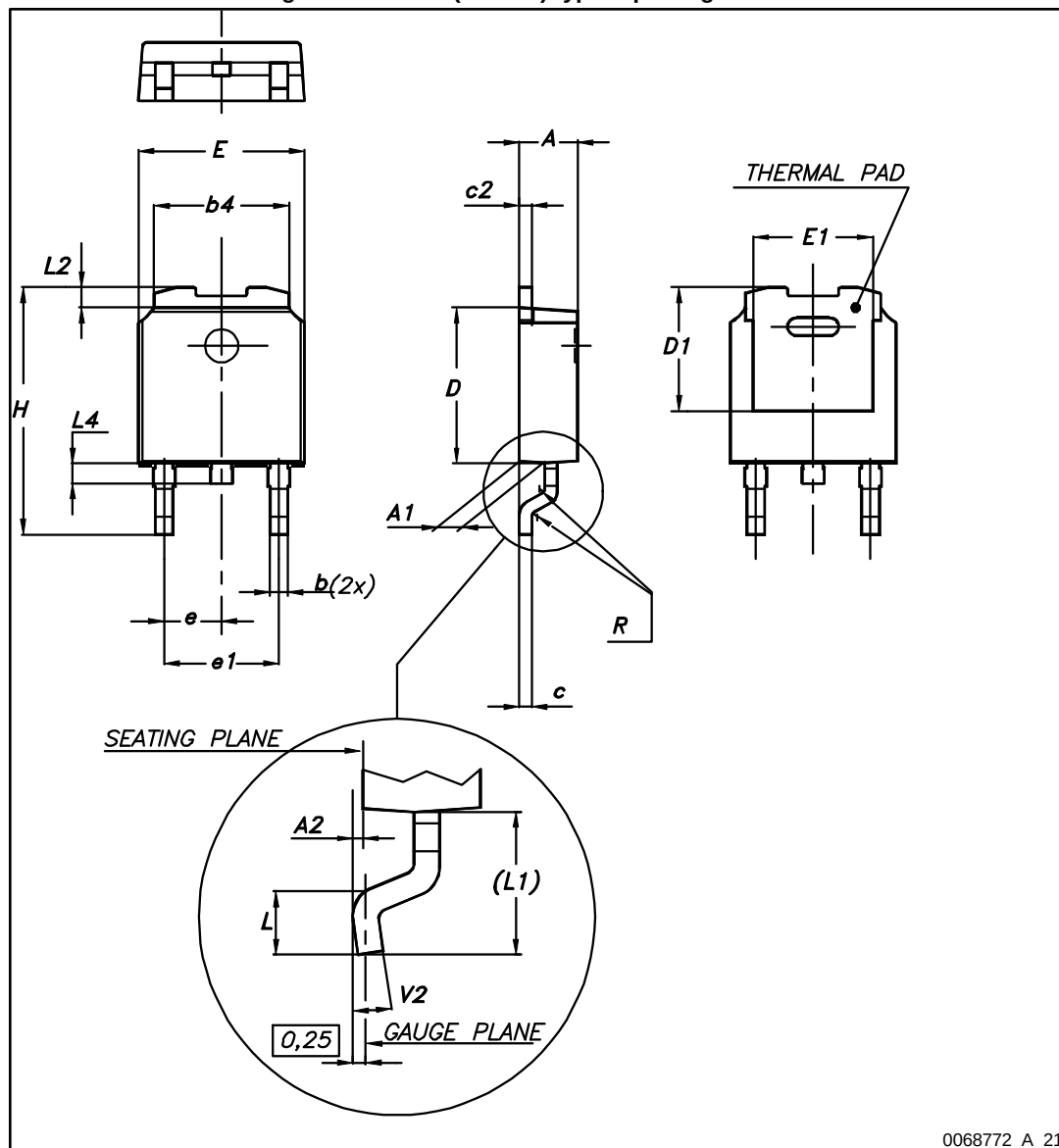


Table 10: D²PAK tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base quantity		1000
P2	1.9	2.1	Bulk quantity		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

4.3 DPAK (TO-252) type A package information

Figure 25: DPAK (TO-252) type A package outline

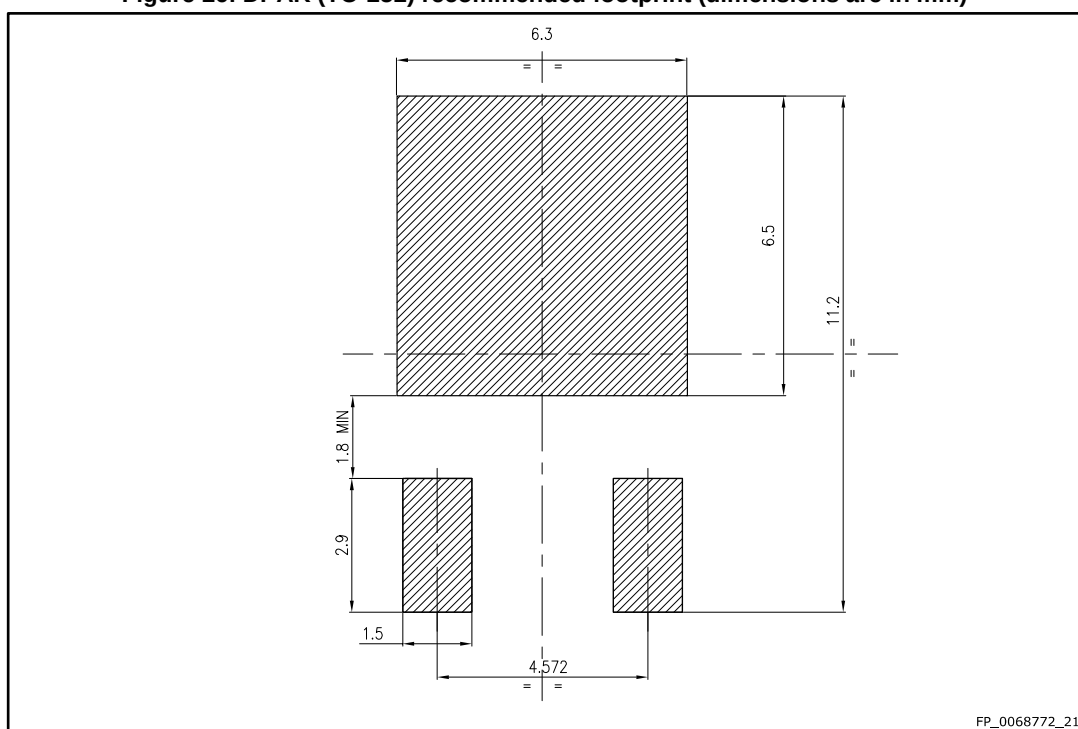


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Table 11: DPAK (TO-252) type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1	4.95	5.10	5.25
E	6.40		6.60
E1	4.60	4.70	4.80
e	2.16	2.28	2.40
e1	4.40		4.60
H	9.35		10.10
L	1.00		1.50
(L1)	2.60	2.80	3.00
L2	0.65	0.80	0.95
L4	0.60		1.00
R		0.20	
V2	0°		8°

Figure 26: DPAK (TO-252) recommended footprint (dimensions are in mm)



4.4 DPAK (TO-252) packing information

Figure 27: DPAK (TO-252) tape outline

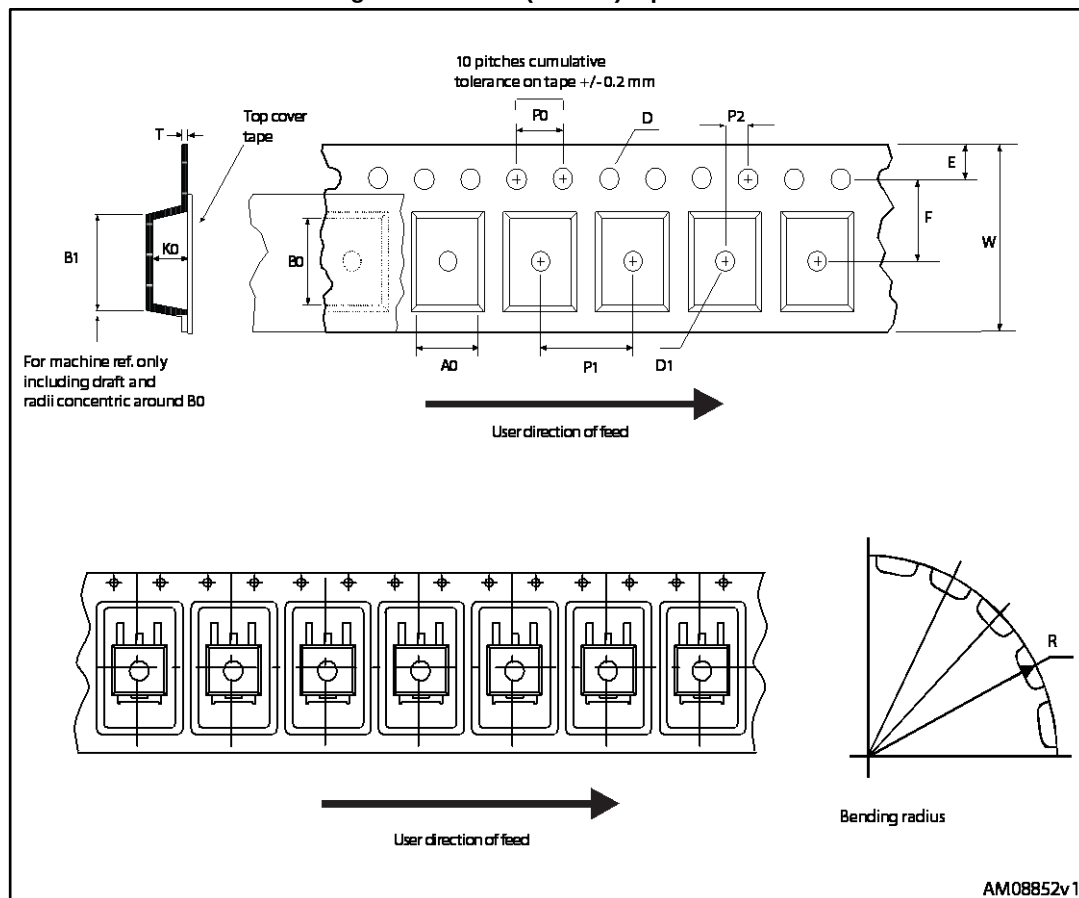


Figure 28: DPAK (TO-252) reel outline

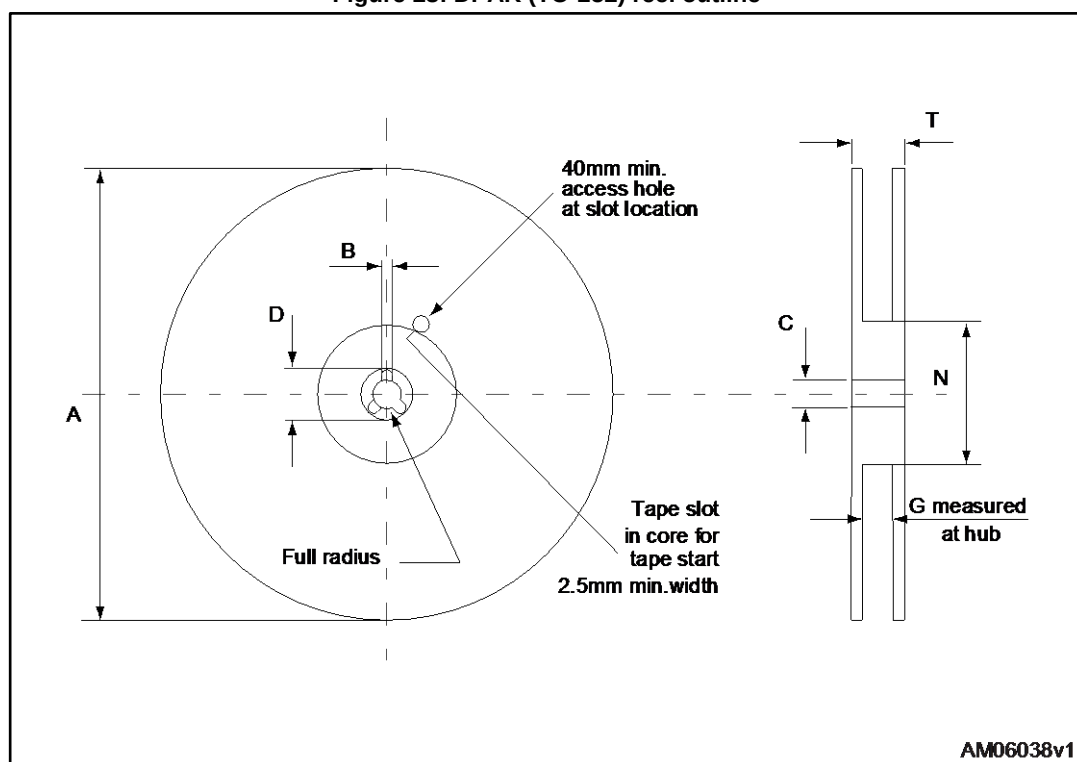


Table 12: DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

4.5 TO-220FP package information

Figure 29: TO-220FP package outline

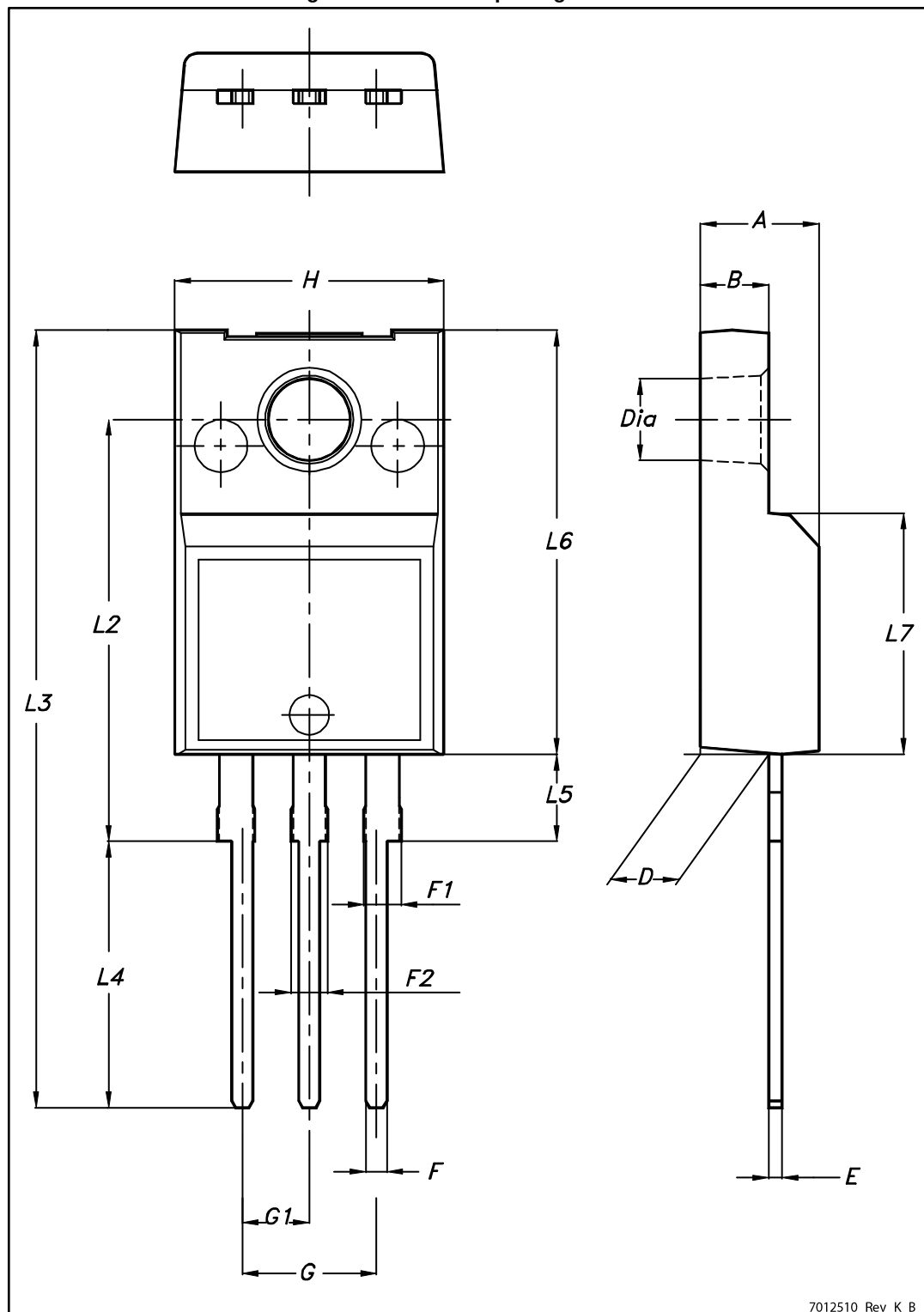


Table 13: TO-220FP package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

4.6 TO-220 type A package information

Figure 30: TO-220 type A package outline

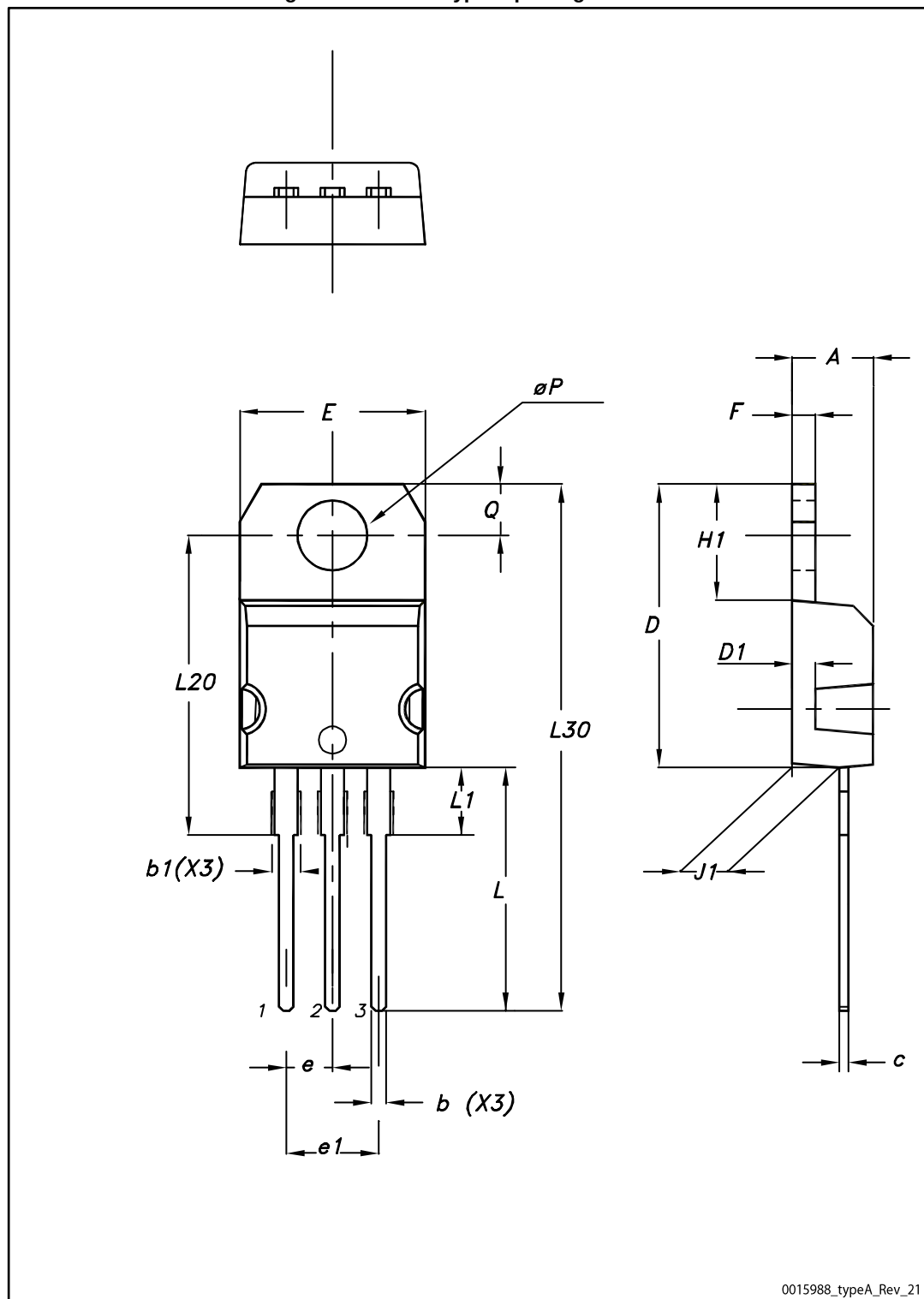


Table 14: TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.55
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10.00		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13.00		14.00
L1	3.50		3.93
L20		16.40	
L30		28.90	
øP	3.75		3.85
Q	2.65		2.95

5 Revision history

Table 15: Document revision history

Date	Revision	Changes
29-Jun-2010	1	First release.
09-Sep-2010	2	Some values changed in <i>Table 2</i> .
22-Dec-2010	3	Document status promoted from preliminary data to datasheet.
24-Sep-2013	4	Added device in TO-220. Updated <i>Table 1: Device summary</i> , <i>Table 3: Thermal data</i> and <i>Section 4: Package mechanical data</i> accordingly.
19-Sep-2016	5	Added the order codes STGB3HF60HD and STGF3HF60HD. Added TO-220FP and D ² PAK packages. Updated <i>Table 1: "Device summary"</i> , <i>Section 1: "Electrical ratings"</i> , <i>Section 4: "Package information"</i> . Minor text changes.

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Компания «Океан Электроники» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Поставка оригинальных импортных электронных компонентов напрямую с производств Америки, Европы и Азии, а так же с крупнейших складов мира;
- Широкая линейка поставок активных и пассивных импортных электронных компонентов (более 30 млн. наименований);
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Помощь Конструкторского Отдела и консультации квалифицированных инженеров;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Поставка электронных компонентов под контролем ВП;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- При необходимости вся продукция военного и аэрокосмического назначения проходит испытания и сертификацию в лаборатории (по согласованию с заказчиком);
- Поставка специализированных компонентов военного и аэрокосмического уровня качества (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Actel, Aeroflex, Peregrine, VPT, Syfer, Eurofarad, Texas Instruments, MS Kennedy, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Компания «Океан Электроники» является официальным дистрибьютором и эксклюзивным представителем в России одного из крупнейших производителей разъемов военного и аэрокосмического назначения «JONHON», а так же официальным дистрибьютором и эксклюзивным представителем в России производителя высокотехнологичных и надежных решений для передачи СВЧ сигналов «FORSTAR».



JONHON

«JONHON» (основан в 1970 г.)

Разъемы специального, военного и аэрокосмического назначения:

(Применяются в военной, авиационной, аэрокосмической, морской, железнодорожной, горно- и нефтедобывающей отраслях промышленности)

«FORSTAR» (основан в 1998 г.)

ВЧ соединители, коаксиальные кабели,
кабельные сборки и микроволновые компоненты:

(Применяются в телекоммуникациях гражданского и специального назначения, в средствах связи, РЛС, а так же военной, авиационной и аэрокосмической отраслях промышленности).



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